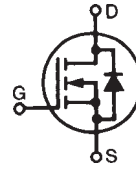


PolarHV™ HiPerFET Power MOSFET

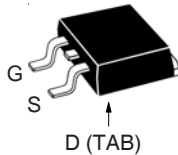
N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

IXFA10N80P
IXFP10N80P
IXFQ10N80P
IXFH10N80P

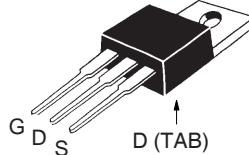


$V_{DSS} = 800V$
 $I_{D25} = 10A$
 $R_{DS(on)} \leq 1.1\Omega$
 $t_{rr} \leq 250ns$

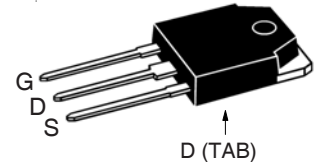
TO-263 AA (IXFA)



TO-220AB (IXFP)

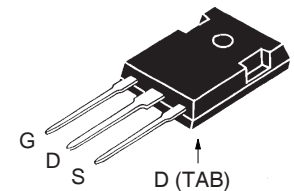


TO-3P (IXFQ)



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	800	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	800	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ C$	10	A
I_{DM}	$T_C = 25^\circ C$, Pulse Width Limited by T_{JM}	30	A
I_A	$T_C = 25^\circ C$	5	A
E_{AS}	$T_C = 25^\circ C$	600	mJ
dV/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$	10	V/ns
P_D	$T_C = 25^\circ C$	300	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	1.6mm (0.062) from Case for 10s	300	$^\circ C$
T_{SOLD}	Plastic Body for 10s	260	$^\circ C$
M_d	Mounting Torque (TO-220, TO-247)	1.13 / 10	Nm/lb.in.
Weight	TO-263	2.5	g
	TO-220	3.0	g
	TO-3P	5.5	g
	TO-247	6.0	g

TO-247 (IXFH)



G = Gate D = Drain
S = Source TAB = Drain

Features

- International Standard Packages
- Avalanche Rated
- Low Package Inductance
- Easy to Drive and to Protect

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Switched-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Laser Drivers
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions ($T_J = 25^\circ C$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	800		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 2.5mA$	3.0		V
I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 150^\circ C$			25 μA
				500 μA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1			1.1 Ω

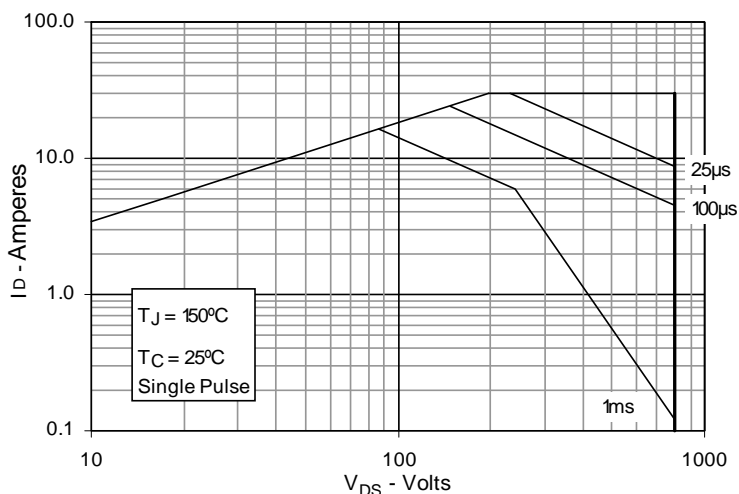
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
g_{fs}	$V_{DS} = 20\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1	7	11	S
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		2050	pF
C_{oss}			172	pF
C_{rss}			16	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 5\Omega$ (External)		21	ns
t_r			22	ns
$t_{d(off)}$			62	ns
t_f			22	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$		40	nC
Q_{gs}			12	nC
Q_{gd}			14	nC
R_{thJC}				0.42 $^\circ\text{C/W}$
R_{thCS}	(TO-220)		0.50	$^\circ\text{C/W}$
R_{thCS}	(TO-247 & TO-3P)		0.25	$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
I_S	$V_{GS} = 0\text{V}$			10 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			30 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1			1.5 V
t_{rr}	$I_F = 10\text{A}$, $V_{GS} = 0\text{V}$ $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$		200	250 ns
I_{RM}			3.0	A
Q_{RM}			0.6	μC

Note 1. Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2\%$

Fig. 1. Forward-Bias Safe Operating Area



IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 2. Output Characteristics
@ 25°C

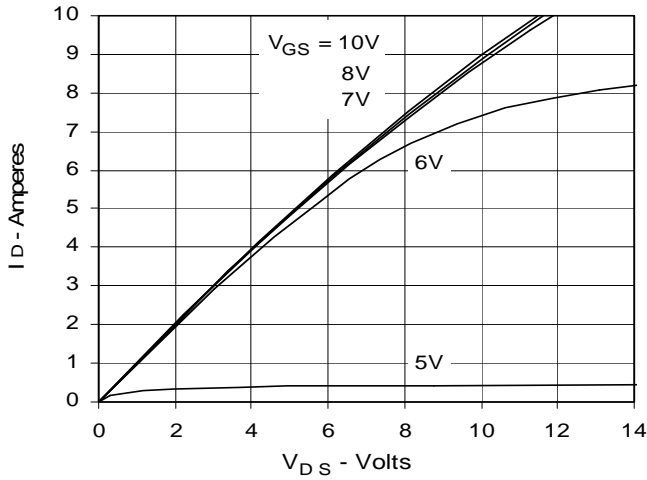


Fig. 3. Extended Output Characteristics
@ 25°C

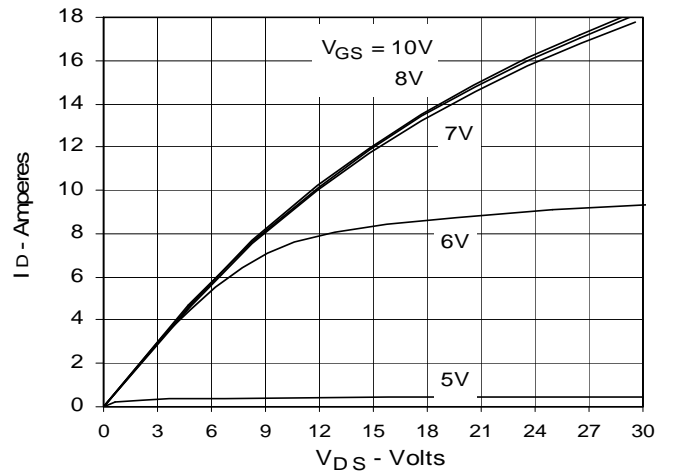


Fig. 4. Output Characteristics
@ 125°C

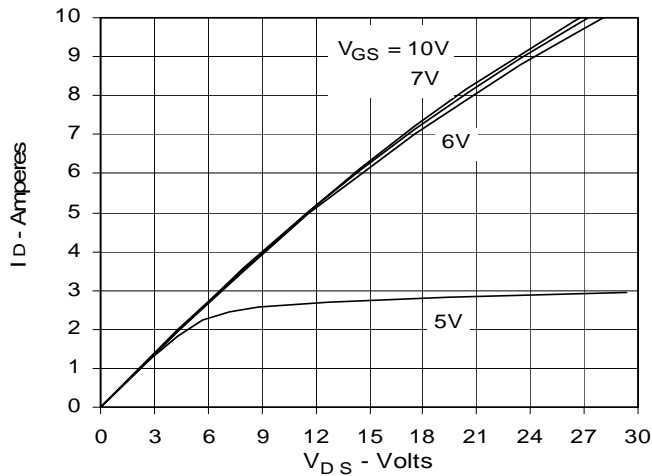


Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Junction Temperature

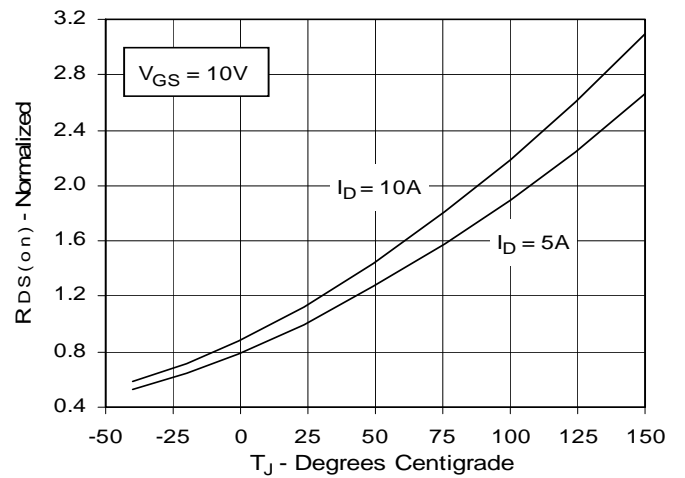


Fig. 6. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. I_D

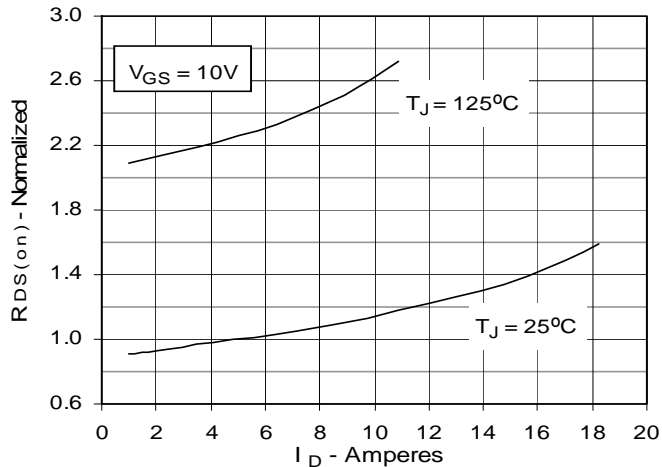


Fig. 7. Drain Current vs. Case Temperature

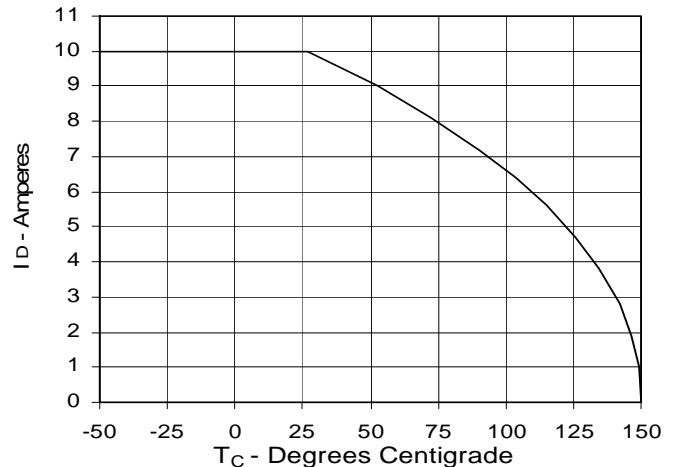


Fig. 8. Input Admittance

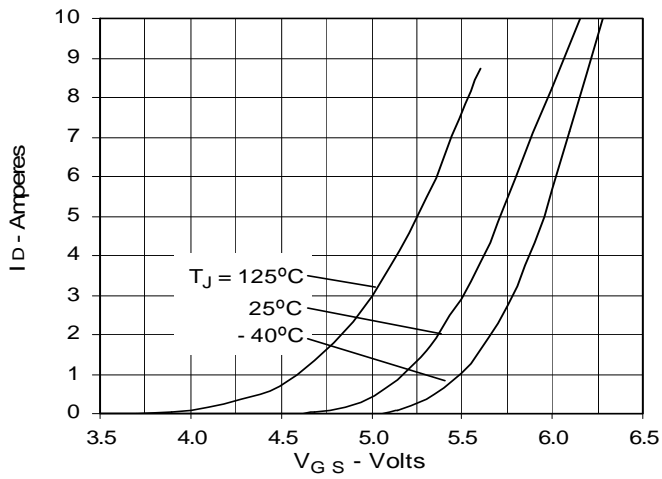


Fig. 9. Transconductance

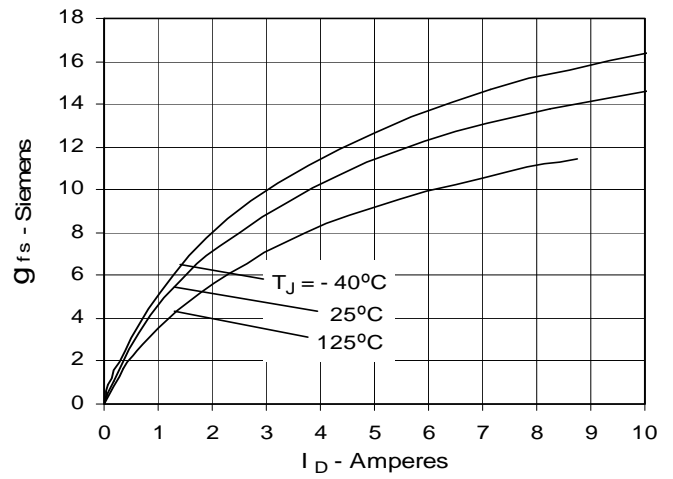


Fig. 10. Source Current vs. Source-To-Drain Voltage

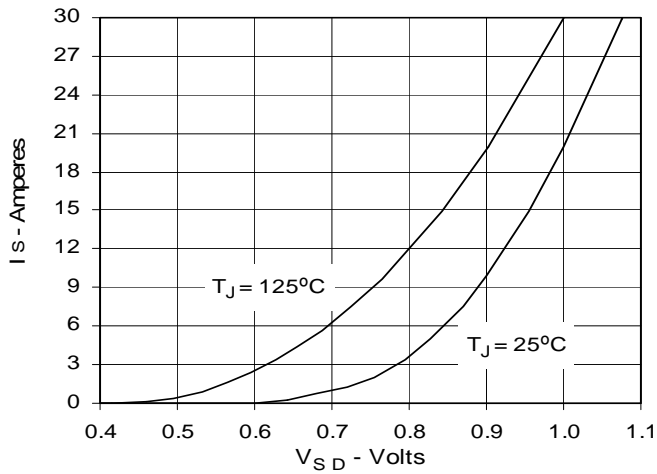


Fig. 11. Gate Charge

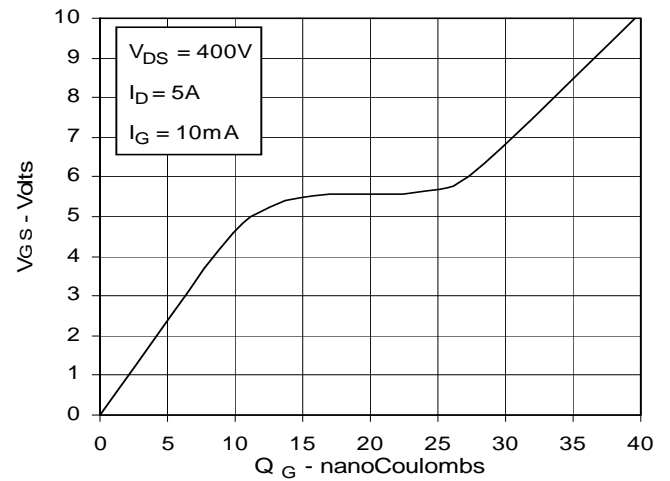


Fig. 12. Capacitance

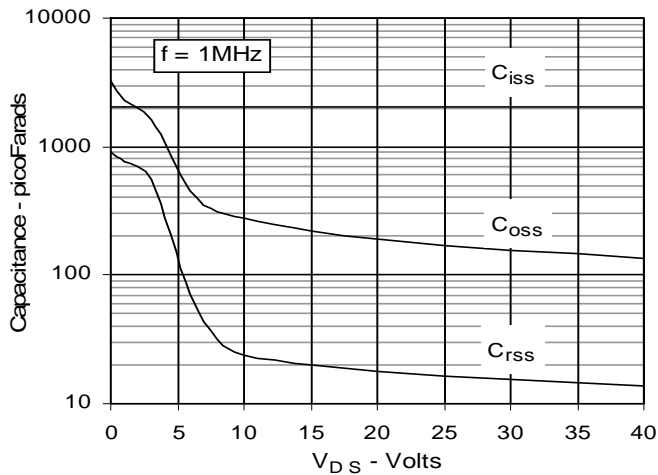


Fig. 13. Maximum Transient Thermal Impedance

